

### KSC5024

### High Voltage and High Reliabilty

- High Speed Switching
- Wide SOA



### **NPN Silicon Transistor**

### **Absolute Maximum Ratings** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter- Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	10	Α
I <sub>CP</sub>	Collector Current (Pulse)	20	Α
I <sub>B</sub>	Base Current	3	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	90	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 1 \text{mA}, I_E = 0$	800			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	500			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = 3.5A$ , $I_{B1} = -I_{B2} = 1.4A$ L = 500 $\mu$ H, Clamped	500			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 500V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.8A$ $V_{CF} = 5V, I_{C} = 4A$	15 8		50	
V <sub>CE</sub> (Sat)	Collector-Emitter Saturation Voltage	$I_C = 4A, I_B = 0.8A$			1	V
V <sub>BE</sub> (Sat)	Base-Emitter Saturation Voltage	$I_C = 4A, I_B = 0.8A$			1.5	V
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		120		pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.8A$		18		MHz
t <sub>on</sub>	Turn ON Time	V <sub>CC</sub> = 200V			0.5	μs
t <sub>s</sub>	Storage Time	I <sub>C</sub> = 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =5A			3	μs
t <sub>f</sub>	Time Fall Time	$R_L = 40\Omega$			0.3	μs

## $\mathbf{h}_{\text{FE}}$ Classificntion

Classification	R	0	Y
h <sub>FE1</sub>	15 ~ 30	20 ~ 40	30 ~ 50

## **Typical Characteristics**

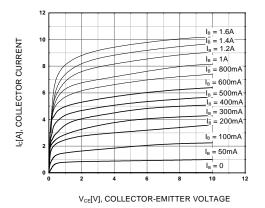


Figure 1. Static Characteristic

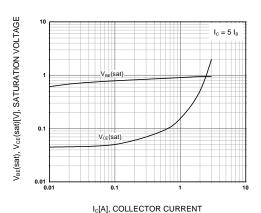


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

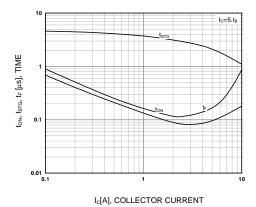


Figure 5. Switching Time

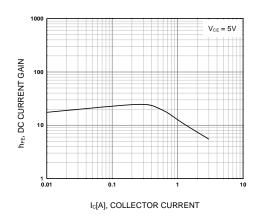


Figure 2. DC current Gain

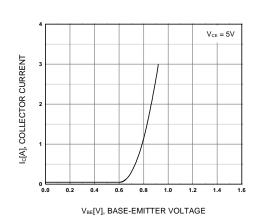


Figure 4. Base-Emitter On Voltage

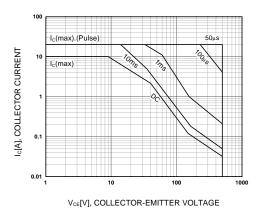


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

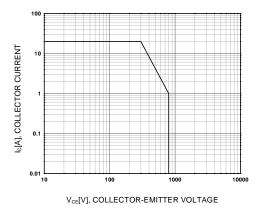


Figure 7. Reverse Bias Safe Operating Area

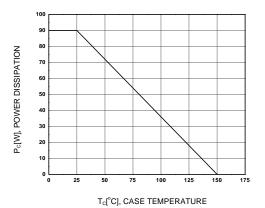
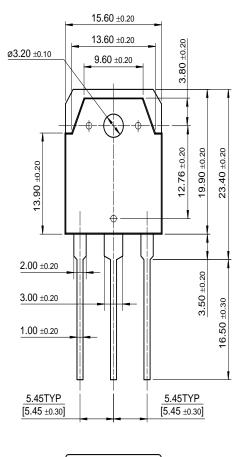
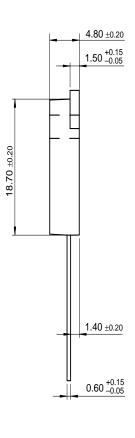


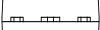
Figure 8. Power Derating

# **Package Demensions**

## TO-3P







Dimensions in Millimeters

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